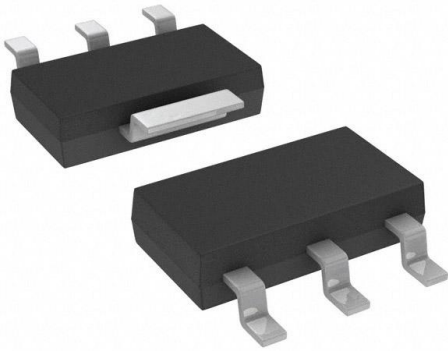


# FZT790A Datasheet

[www.digi-electronics.com](http://www.digi-electronics.com)



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	FZT790A-DG
Manufacturer	<a href="#">onsemi</a>
Manufacturer Product Number	FZT790A
Description	TRANS PNP 40V 3A SOT223-4
Detailed Description	Bipolar (BJT) Transistor PNP 40 V 3 A 100MHz 2 W Surface Mount SOT-223-4



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

DiGi is a global authorized distributor of electronic components.

## Purchase and inquiry

Manufacturer Product Number:

FZT790A

Series:

-

Transistor Type:

PNP

Voltage - Collector Emitter Breakdown (Max):

40 V

Current - Collector Cutoff (Max):

100nA (ICBO)

Power - Max:

2 W

Operating Temperature:

-55°C ~ 150°C (TJ)

Package / Case:

TO-261-4, TO-261AA

Base Product Number:

FZT790

Manufacturer:

onsemi

Product Status:

Active

Current - Collector (Ic) (Max):

3 A

Vce Saturation (Max) @ Ib, Ic:

750mV @ 50mA, 2A

DC Current Gain (hFE) (Min) @ Ic, Vce:

300 @ 10mA, 2V

Frequency - Transition:

100MHz

Mounting Type:

Surface Mount

Supplier Device Package:

SOT-223-4

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0075

Moisture Sensitivity Level (MSL):

1 (Unlimited)

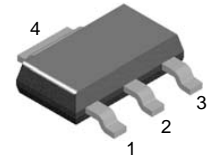
ECCN:

EAR99



# PNP Low Saturation Transistor

## FZT790A



1. Base  
2., 4. Collector  
3. Emitter

**SOT-223**  
**CASE 318H**

### Description

These devices are designed with high current gain and low saturation voltage with collector currents up to 3 A continuous.

### Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### ABSOLUTE MAXIMUM RATINGS (Notes 1, 2)

(Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	-40	V
Collector-Base Voltage	$V_{CBO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current - Continuous	$I_C$	-3	A
Operating and Storage Junction Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- These ratings are based on a maximum junction temperature of  $150^\circ\text{C}$ .
- These are steady-state limits. **onsemi** should be consulted on applications involving pulsed or low-duty-cycle operations.

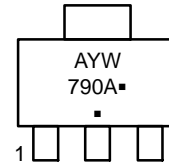
### THERMAL CHARACTERISTICS (Note 3)

(Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Total Power Dissipation	$P_D$	2	W
Dissipation Derate Above $25^\circ\text{C}$	$P_D$	16	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$

- PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
W = Work Week  
790A = Specific Device Code  
■ = Pb-Free Package  
(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

**FZT790A****ELECTRICAL CHARACTERISTICS**(Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Max.	Unit
$BV_{CEO}$	Collector–Emitter Breakdown Voltage	$I_C = -10\text{ mA}, I_B = 0$	-40		V
$BV_{CBO}$	Collector–Base Breakdown Voltage	$I_C = -100\ \mu\text{A}, I_E = 0$	-50		V
$BV_{EBO}$	Emitter–Base Breakdown Voltage	$I_E = -100\ \mu\text{A}, I_C = 0$	-5.0		V
$I_{CBO}$	Collector Cut–Off Current	$V_{CB} = -30\text{ V}, I_E = 0$		-100	nA
		$V_{CB} = -30\text{ V}, I_E = 0, T_A = 100^\circ\text{C}$		-10	$\mu\text{A}$
$I_{EBO}$	Emitter Cut–Off Current	$V_{EB} = -4\text{ V}, I_C = 0$		-100	nA
$h_{FE}$	DC Current Gain (Note 4)	$V_{CE} = -2.0\text{ V}, I_C = -10\text{ mA}$	300		
		$V_{CE} = -2.0\text{ V}, I_C = -500\text{ mA}$	250		
		$V_{CE} = -2.0\text{ V}, I_C = -1.0\text{ A}$	200		
		$V_{CE} = -2.0\text{ V}, I_C = -2.0\text{ A}$	150		
$V_{CE}(\text{sat})$	Collector–Emitter Saturation Voltage (Note 4)	$I_C = -500\text{ mA}, I_B = -5.0\text{ mA}$		-0.25	V
		$I_C = -1.0\text{ A}, I_B = -10\text{ mA}$		-0.45	
		$I_C = -2.0\text{ A}, I_B = -50\text{ mA}$		-0.75	
$V_{BE}(\text{sat})$	Base–Emitter Saturation Voltage (Note 4)	$I_C = -1.0\text{ A}, I_B = -10\text{ mA}$		-1.0	V
$V_{BE}(\text{on})$	Base–Emitter On Voltage (Note 4)	$I_C = -1.0\text{ A}, V_{CE} = -2.0\text{ V}$		-1.0	V
$f_T$	Transition Frequency	$I_C = -50\text{ mA}, V_{CE} = -5.0\text{ V}, f = 50\text{ MHz}$	100		MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2.0\%$

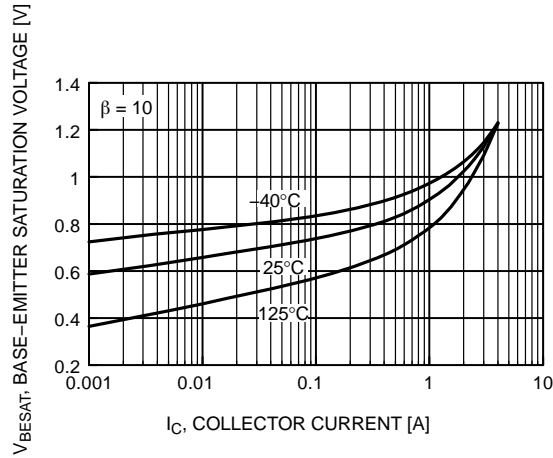
**ORDERING INFORMATION**

Part Number	Top Mark	Package	Shipping <sup>†</sup>
FZT790A	790A	SOT–223 (Pb–Free)	4,000 Units/ Tape & Reel

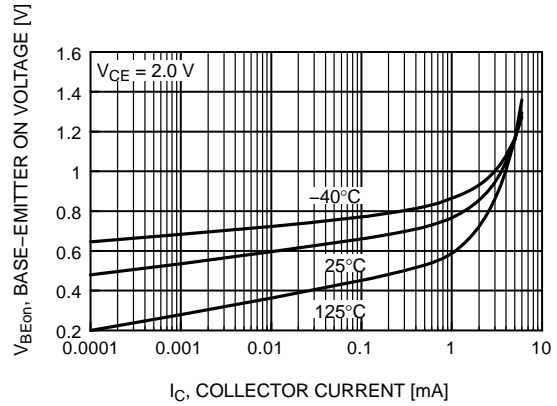
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# FZT790A

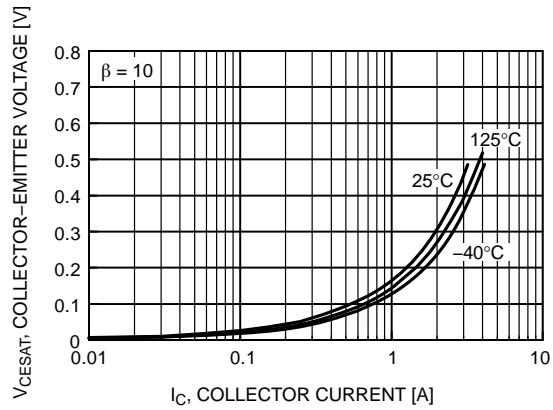
## TYPICAL PERFORMANCE CHARACTERISTICS



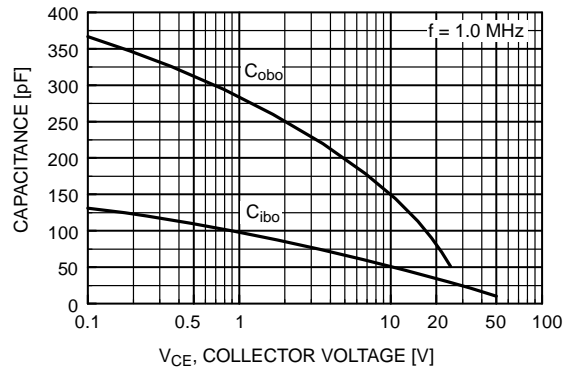
**Figure 1. Base-Emitter Saturation Voltage vs. Collector Current**



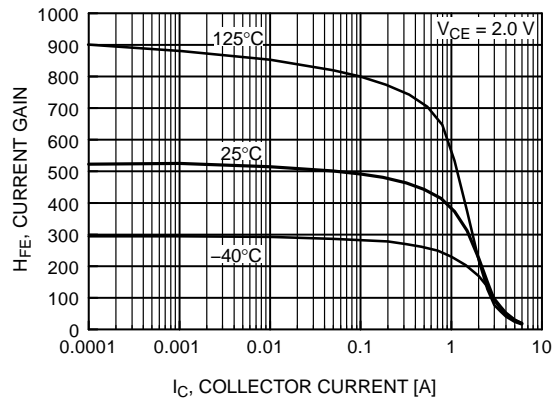
**Figure 2. Base-Emitter On Voltage vs. Collector Current**



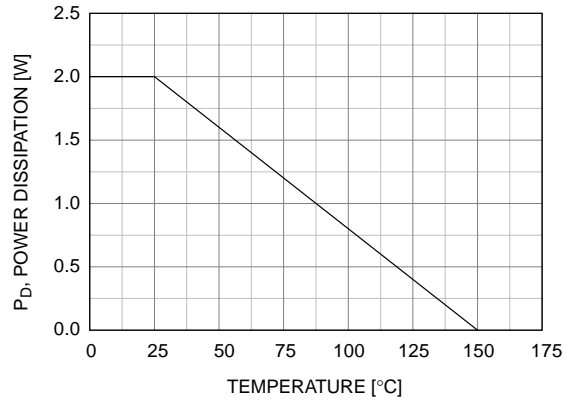
**Figure 3. Collector-Emitter Saturation Voltage vs. Collector Current**



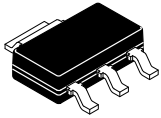
**Figure 4. Input/Output Capacitance vs. Reverse Bias Voltage**



**Figure 5. Current Gain vs. Collector Current**



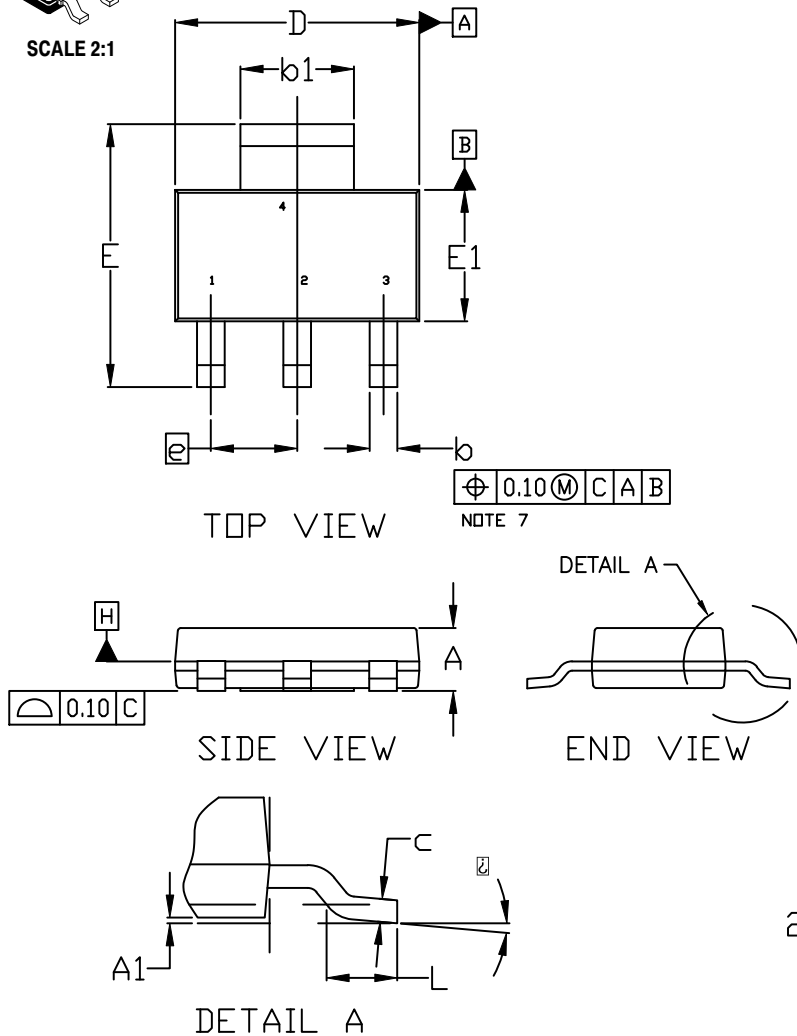
**Figure 6. Power Dissipation vs. Ambient Temperature**



SCALE 2:1

**SOT-223**  
**CASE 318H**  
**ISSUE B**

DATE 13 MAY 2020

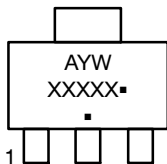


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E1 ARE DETERMINED AT DATUM H. DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. SHALL NOT EXCEED 0.23mm PER SIDE.
4. LEAD DIMENSIONS b AND b1 DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS 0.08mm PER SIDE.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
7. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

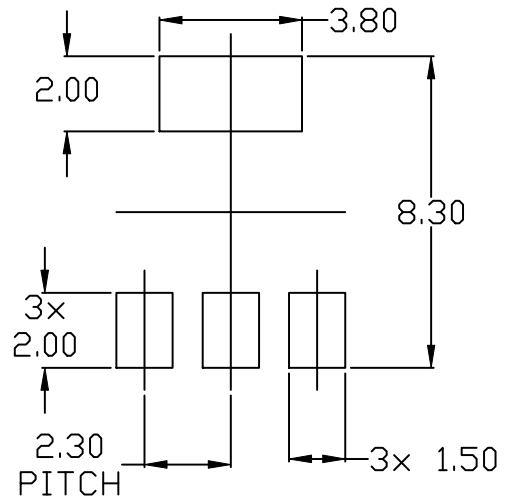
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.80
A1	0.02	0.06	0.11
b	0.60	0.74	0.88
b1	2.90	3.00	3.10
c	0.24	---	0.35
D	6.30	6.50	6.70
E	6.70	7.00	7.30
E1	3.30	3.50	3.70
e	2.30 BSC		
L	0.25	---	---
∠	0°	---	10°

**GENERIC MARKING DIAGRAM\***



- A = Assembly Location
  - Y = Year
  - W = Work Week
  - XXXXX = Specific Device Code
  - = Pb-Free Package
- (Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



**RECOMMENDED MOUNTING FOOTPRINT**

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

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